HCNS1010B

100V N-Channel MOSFET

General Description

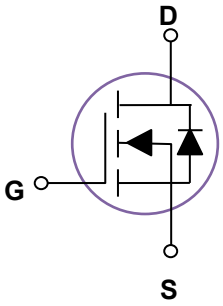
These N-Channel enhancement mode power field effect transistors are using SGT technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

V_{DS}	100V
I_D (at V_{GS}=10V)	63A
$R_{DS(ON)}$ (at V_{GS}=10V)	8.8mΩ(Typ)

100% UIS TESTED!
100% ΔVds TESTED!

PDFN5x6



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current-Continuous	TC=25°C	I_D	63	A
	TC=100°C	I_D	40	A
Maximum Power Dissipation		P_D	83	W
Single pulse avalanche energy(1)		E_{AS}	86	mJ
Junction and Storage Temperature Range		T_J,T_{STG}	-55 To 150	℃

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance junction-case	$R_{\theta Jc}$		1.5	℃ /W
Thermal Resistance junction-to-Ambient	$R_{\theta JA}$		62	℃ /W

Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V,V_{GS}=0V			1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	2.0	3.0	4.0	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=20A		8.8	11.0	mΩ
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		1370		pF
C_{oss}	Output Capacitance			291		pF
C_{rss}	Reverse Transfer Capacitance			6.2		pF
SWITCHING PARAMETERS						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=50V,I_D=1A, V_{GS}=10V, R_G=6Ω		11		nS
t_r	Turn-on Rise Time			20		nS
$t_{d(off)}$	Turn-Off Delay Time			20		nS
t_f	Turn-Off Fall Time			25		nS
Q_g	Total Gate Charge	V_{DS}=50V,I_D=20A, V_{GS}=10V		21		nC
Q_{gs}	Gate-Source Charge			5.4		nC
Q_{gd}	Gate-Drain Charge			5.3		nC
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz		2.0		Ω
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_{SD}=1A		0.7	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	I_F = 20A, dI_F/dt = 100A/μS		48		ns
Q_{rr}	Body Diode Reverse Recovery Charge			79		nC

Note：

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=50V,V_{GS}=10V,L=0.5mH, Starting TJ=25℃
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

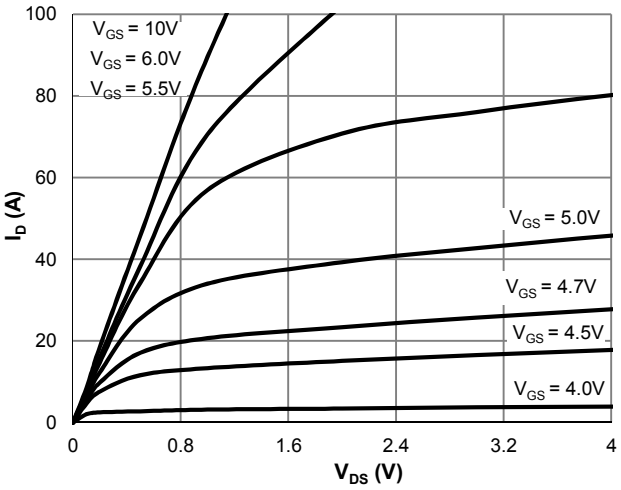


Figure 1: Saturation Characteristics

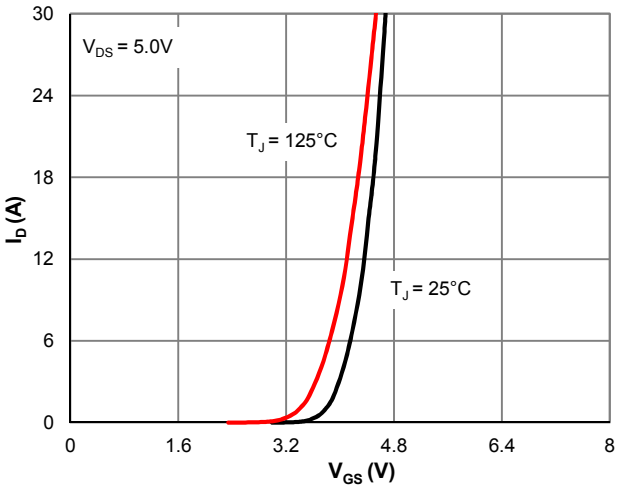


Figure 2: Transfer Characteristics

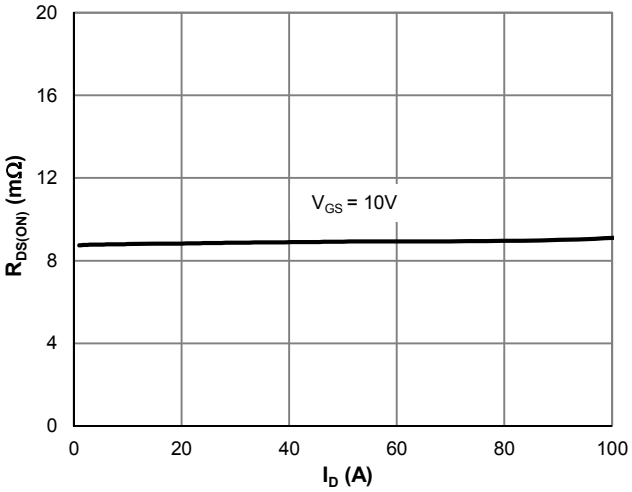


Figure 3: $R_{DS(ON)}$ vs. Drain Current

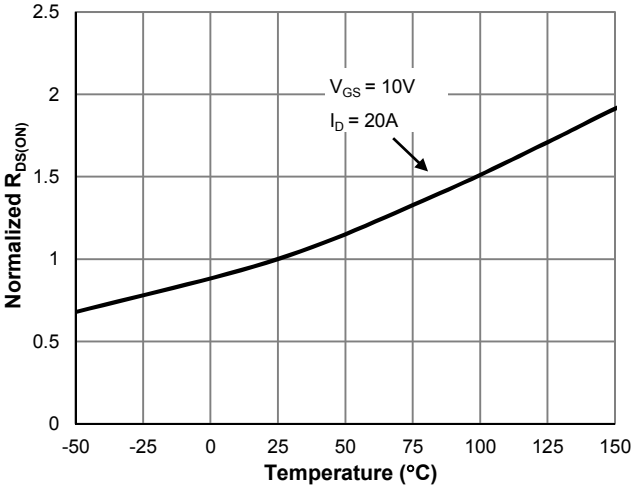


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

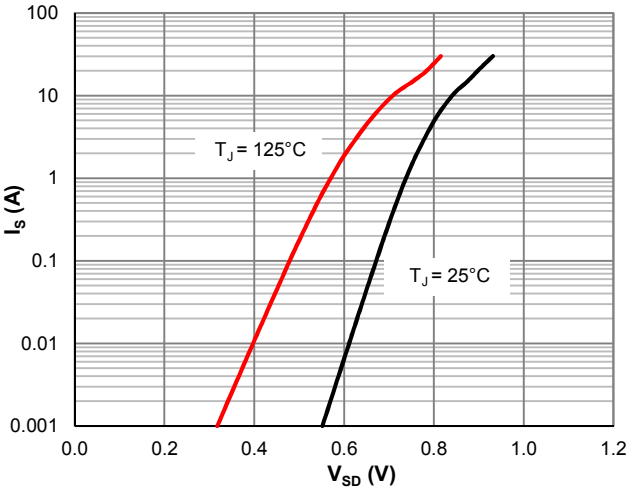


Figure 5: Body-Diode Characteristics

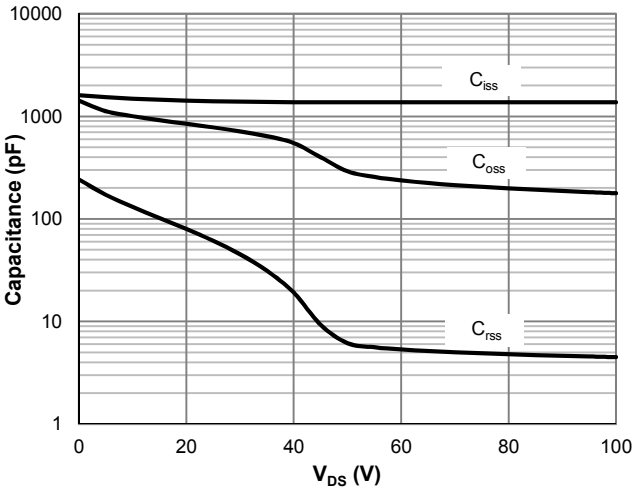


Figure 6: Capacitance Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

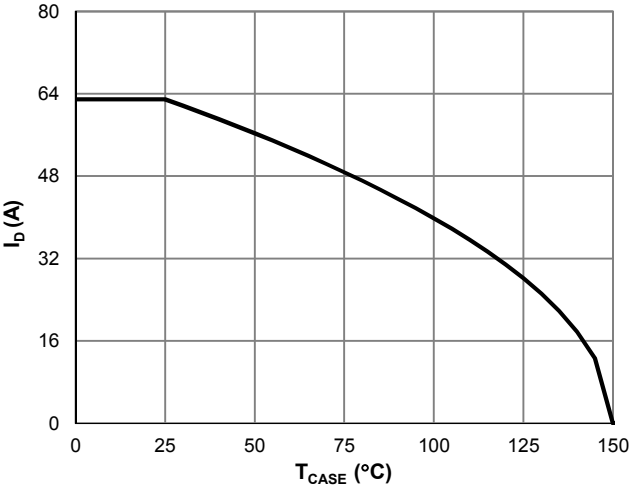


Figure 7: Current De-rating

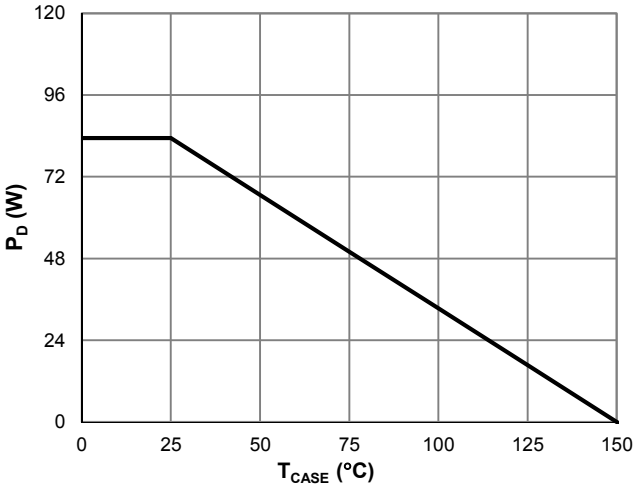


Figure 8: Power De-rating

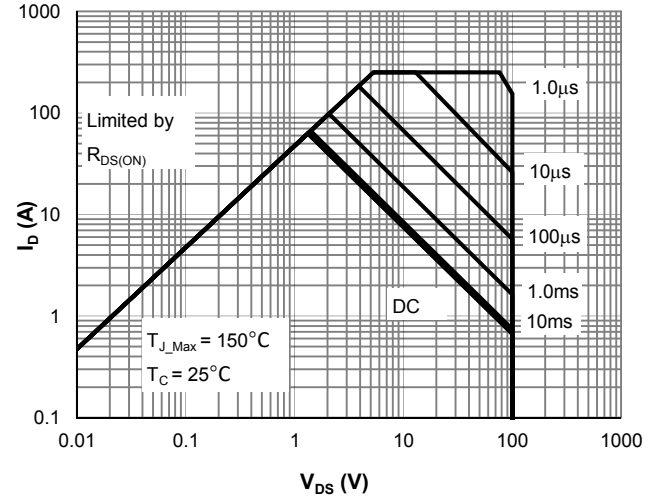


Figure 9: Maximum Safe Operating Area

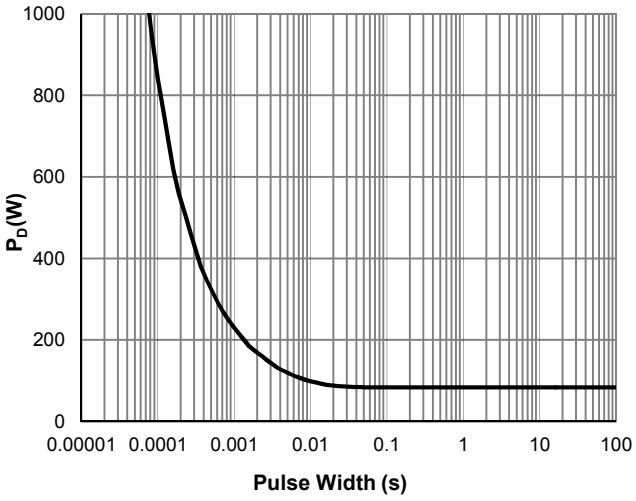


Figure 10: Single Pulse Power Rating, Junction-to-Case

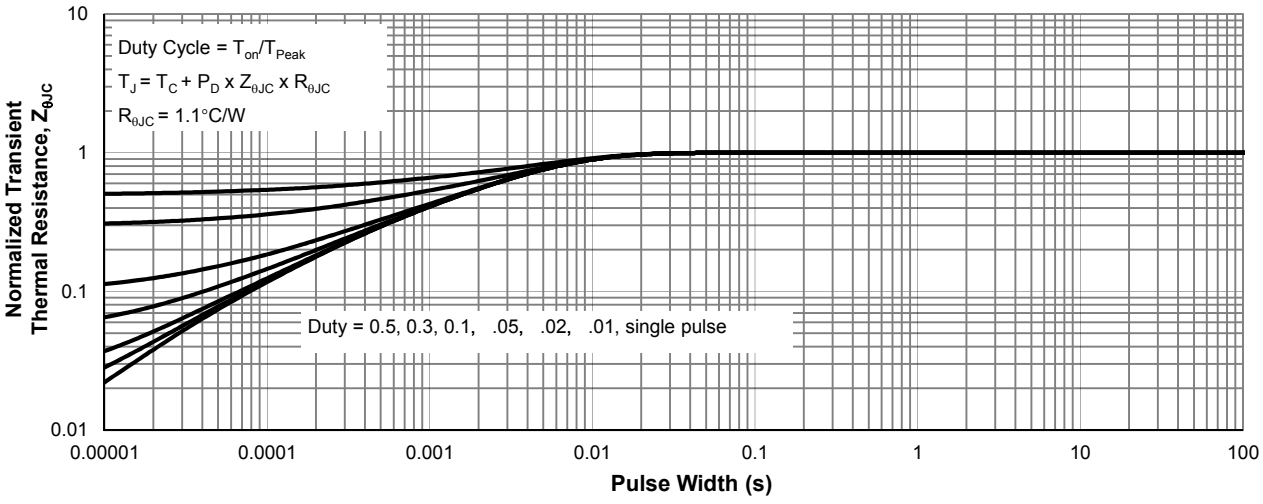
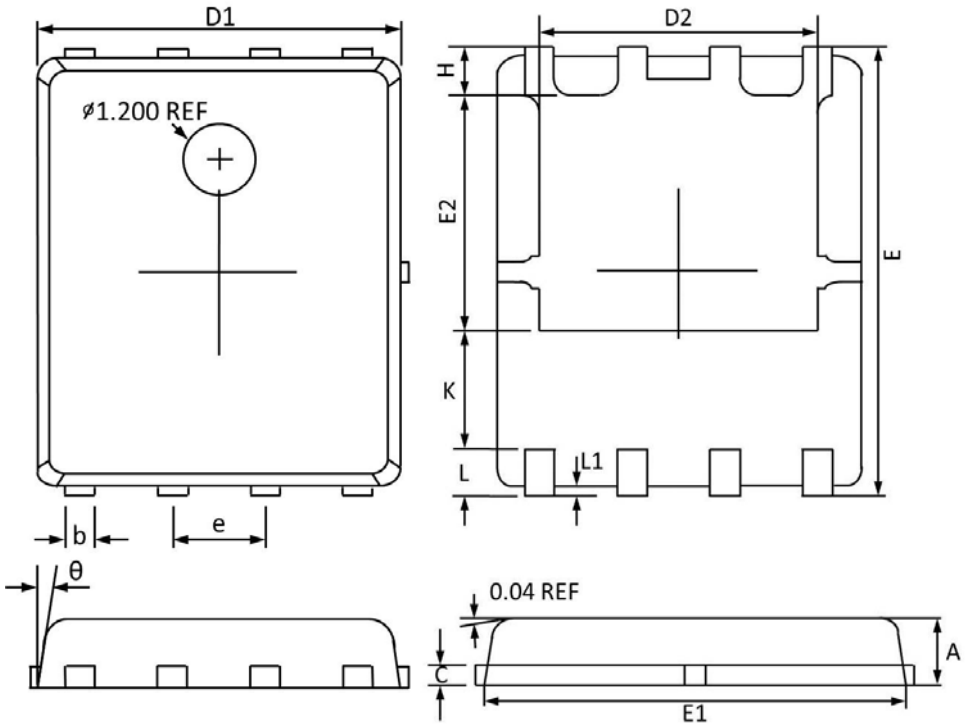


Figure 11: Normalized Maximum Transient Thermal Impedance

PDFN5x6 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
θ	12°	0°	12°	0°